# E lectron-electron interactions and the phase diagram of a graphene bilayer 

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#### Abstract

We study the e ects of long and short-range electron-electron interactions in a graphene bilayer. $U$ sing a variational wavefunction technique we show that in the presence of long-range Coulom b interactions the clean bilayer is alw ays unstable to electron and hole pocket form ation $w$ ith a nite ferrom agnetic polarization. Furtherm ore, we argue that short-range electron-electron interactions lead to a staggered orientation of the ordered ferrom agnetic $m$ om ent in each layer (that is, c-ax is antiferrom agnetism ). We also com $m$ ent on the e ects of doping and trigonal distortions of the electronic bands.


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## I. INTRODUCTION

The recent developm ents in the eld of carbon physics, where a few layers or even single layers of graphene have been isolated, have show $n$ that the physics of these system $s$ is unconventional from the point of view of traditional sem iconductor and Ferm i-liquid physics ${ }^{1,2}$. The electronic dispersion of graphene close to the tw O Kpoints of the $B$ rillouin zone can be written $a s^{3}: E \quad(p)=$
 sion is valid for two-dim ensionalm om entum $p=\left(p_{x} ; p_{y}\right)$ such that $\mathrm{pj}<\quad$ where is a m om entum cut-o of the order of the inverse of the lattice spacing a). This dispersion relation is identical to the one of $D$ irac electrons w ith \speed of light" given by $\mathrm{V}_{\mathrm{F}}$. In this case the electron e ective $m$ ass, $m$, is zero, and the density of states vanishes at the $K$-point. T he vanishing of the effective $m$ ass, the interplay of interactions, disorder, and extended defects, lead to anom alous behavior in $m$ any physical properties ${ }^{4,5}$.

The capability of experim entally controlling the num ber of graphene layers opens up the eld for the study of the e ect of interlayer coupling in a strongly interacting two-dim ensional system. Interlayer coupling is a controversial topic in the graphite literature where the precise nature of the coupling betw een graphene planes is unsettled 6,7 . A nother im portant issue in carbon research has to do w th the weak ferrom agnetism in highly disordered graphite that have been observed in experim ents ${ }^{8}$ but is still a theoretically open problem 9,10 .

It is well-known that the low-density electron gas w ith long-range $C$ oulom b interactions in tw o and three dim ensions is unstable tow ard a ferrom agnetic state. T he original argum ent due to $B$ loch relies on a variational calculation of the ground state energy ${ }^{11}$. Recently this approach w as used to look for a possible ferrom agnetic instability in a single layer of graphene ${ }^{10}$. The param eter that controls the relative strength betw een kinetic and C oulom b energies is the dim ensionless coupling, $g=e^{2} 0^{1}=V_{F}$; $(h=1)$ where $e$ is the electric charge $(~(~=14: 4 \mathrm{eV} \mathrm{A})$,
and 0 is the graphene dielectric constant ( $0 \quad 1$ ). In that case, ferrom agnetism is only found for values of $g$ larger than a critical value, $g_{c} \quad 5: 3$, which is larger than its estim ated value in graphene ( $g$ 2:1). An analysis based on short-range interactions seem $s$ to con $m$ this picture ${ }^{5}$.

In this paper we use a sim ilar variational technique to study a clean graphene bilayer w here we include the hopping betw een graphene planes. U nlike the case of a single layer, we nd that the bilayer is alw ays unstable tow ard a ferrom agnetic state $w$ th form ation of electron and hole pockets w th a polarization of the order of $10{ }^{6}$ to $10{ }^{5}$ electrons per carbon. T his result $m$ ay have direct im plications for the interpretation of the $m$ agneto-transport data in graphitic devioes ${ }^{12}$.

The paper is organized as follow s: In Section the m odel is introduced. In Section $I$ III we explain the variational calculation and present the phase diagram. T he in uence of other hopping param eters on the instability are discussed in Section IV. Section $V$ includes the results for the low -energy susceptibilities and a discussion of short range interactions. The conclusions of the paper are to be found in Section VI. W e also include appendioes w ith som em athem atical details.

## II. THEMODEL

The lattioe structure for the bilayer which is just one unit cell of graphite is depicted in Fig. 11. For sim plicity we m odel the system by the nearest neighbor tightbinding H am iltonian:

$$
\begin{align*}
& H_{t . b}=t_{<m ; n>}^{X}\left(C_{A_{i} ; m}^{y} ; C_{B_{i} ; n} ;+h . C .\right) \\
& X^{\text {i }} \\
& \text { t. } \quad\left(C_{\mathrm{A}_{1} ; m}^{\mathrm{y}} ; \mathrm{C}_{\mathrm{A}_{2} ; \mathrm{m}} ;+\mathrm{h} . \mathrm{C} .\right) \text {; }  \tag{1}\\
& \text { m ; }
\end{align*}
$$

where $\mathrm{C}_{\mathrm{a}_{i} ; m}$; ( $\mathrm{C}_{\mathrm{a}_{\mathrm{i}} ; m}^{\mathrm{y}}$; ) anninilates (creates) an electron on site $m$ of the sublattice $a(a=A ; B)$ of plane i


F IG . 1: (C olor online) Lattice structure of the bilayer. The A-sublattices are indicated by the darker spheres.
( $\mathrm{i}=1 ; 2$ ), w ith spin $(=\boldsymbol{=} ; \#)$, $\mathrm{t}(\mathrm{t} \quad 3 \mathrm{eV})$ is the inplane hopping energy and $t$ ? ( $t$ ? $0: 35 \mathrm{eV}$ in graphité ) is the hopping energy betw een atom $\mathrm{A}_{1}$ and atom $\mathrm{A}_{2}$ (see Fig.(1). A sim ilar tight-binding H am iltonian for graphite and the single graphene layer was studied long ago by W allace ${ }^{3}$. At low energies and long wavelengths, the kinetic H am iltonian can be expanded around the K ( $\mathrm{K}^{\prime}$ ) points in the $B$ rillouin zone. T he resulting $H$ am iltonian can be w ritten as:

$$
\begin{equation*}
H_{k i n}={ }_{Q}^{X}{ }_{Q}^{Y} K(p) \quad Q \text {; } \tag{2}
\end{equation*}
$$

w ith Q denoting $(\mathrm{p} ; \mathrm{i} ; \quad ; \mathrm{a})$ and ${ }_{Q}^{\mathrm{y}}=$ $\left(C_{p ; r A_{1} ; ~ ; a}^{y} ; C_{p ; r B_{1} ; ~ ; a}^{y} ; C_{p ; r A_{2} ; ~ ; a}^{y} ; C_{p ; r B_{2} ; ~ ; a}^{y}\right)$. Here, $\mathrm{C}_{\mathrm{p}}^{\mathrm{p}} ; \mathrm{i} ;$;a ( $\left.\mathrm{p} ; ~ ; ~ ; a\right)$ creates (annihilates) an electron with m om entum p , on sublattice $\mathrm{i}(=A ; B)$ of plane i $(i=1 ; 2)$, with spin $(=" ; \#)$ at the $K$-point a $(a=1 ; 2)$ in the $B$ rillouin zone, and
is the kinetic energy $m$ atrix where $(p)=\tan ^{1}\left(p_{y}=p_{x}\right)$. W e have set $\mathrm{v}_{\mathrm{F}}=1=$, so that the energy is m easured in units of the in-plane hopping, $t$, and distance is $m$ easured in units of carbon-carbon distance a (a 1:42 A) ${ }^{6}$.

The kinetic term can be diagonalized by a unitary transform ation: $p=M p_{p}$, where $M p$ is given in $A p-$
 where the four energy bands are given by:

$$
\begin{aligned}
& E_{1}(\mathrm{p})=\mathrm{t}_{\mathrm{p}}=2+\mathrm{E}(\mathrm{p}) ; \\
& \mathrm{E}_{2}(\mathrm{p})=\mathrm{t}_{?}=2 \mathrm{E}(\mathrm{p}) ; \\
& \mathrm{E}_{3}(\mathrm{p})=\mathrm{t}_{?}=2+\mathrm{E}(\mathrm{p}) ; \\
& \mathrm{E}_{4}(\mathrm{p})=\mathrm{t}_{\mathrm{p}}=2 \mathrm{E}(\mathrm{p}) ;
\end{aligned}
$$

where $E(p)=P \overline{t_{?}^{2}=4+p^{2}}$. The bands are sketched in F ig. 2. Any state of the system can be labeled in term $s$ of the occupation of each band, $n_{i ;} ; a(p)$, with


FIG. 2: B and dispersions near the $K$-points in the bilayer. $B$ ands are labeled by the num bers 14 as in the text.
$i=1 ; 2 ; 3 ; 4$. The non-interacting ground state has degeneracy 4 per m om entum, per plane, due to the SU (2) spin rotation symmetry and the $Z_{2}$ real space sublattioe exchange symmetry (at low energies this symmetry becom es SU (2) for the continuous rotation of the K and $\mathrm{K}^{\prime}$ states in m om entum spaœ), and occupation at half- lling, given by: $n_{1} ; ~ ; a(p)=0, n_{2} ; ~ ; a(p)=1$, $\mathrm{n}_{3} ;$; $(\mathrm{p})=0$ and $\mathrm{n}_{4} ;$; $(\mathrm{p})=1$. Hence, the presence of $t_{\text {? }}$ does not $m$ ix the spins or the $K-$ points. H ow ever, the tw O D irac cones transform into vertex touching hyperbolae, and for $p$ t? the electrons acquire an e ective $m$ ass, $m \quad t=2$.

The Coulomb interaction in the bilayer is conveniently written in term $s$ of the Fourier com ponents of sym $m$ etric and anti-symmetric combinations of the payer densities, $\quad(q)=1(q) \quad 2(q)$, where $i(q)=$


$$
\begin{equation*}
H_{I}=\frac{1}{2 S}_{q \notin 0}^{X} X \quad \text { (q)V (q) ( q); } \tag{4}
\end{equation*}
$$

where $V(q)=2 e^{2}\left(1 \quad e^{q d}\right)=2{ }_{0} q, S$ is the area of the system, and $d$ is the interplane distance ( $d$ 2:4a $3: 35 \mathrm{~A}, \mathrm{~d} 3: 7$ ). W e are going to show that in the presence of Eq. (4) the non-interacting ground state is unstable. To perform the calculation it is convenient to express the density operators in the diagonal ba-
 w rite the exchange energy associated w ith Eq. (4) as:

$$
\begin{array}{r}
\frac{E_{e x}}{S}=\frac{1}{2}^{Z} \frac{d p}{(2)^{2}} \frac{d^{2} p^{0}}{(2)^{2}}=X \\
i j i ; j ; a  \tag{5}\\
i\left(p^{0} ; p\right){ }_{j i}\left(p ; p^{0}\right) n_{i ;} ;\left(p^{0}\right) n_{j ;} ; a(p) V\left(p^{0} p\right):
\end{array}
$$

The de nitions of the $m$ atrices and som em ore details about the exchange interaction for B loch electrons and Eq. (5) are given in A ppendix B.
III. VARIATIONALCALCULATION AND PHASE D IA GRAM

C onsider the half- lled case $w$ ith a variational state w ith one electron pocket in the spin up channel and one hole pocket in the spin dow $n$ channel at each $K-$ point: $\mathrm{n}_{1 ; " ; a}(\mathrm{p})=(\mathrm{Q} \quad \mathrm{p}), \mathrm{n}_{1 ; \# ;}(\mathrm{p})=0, \mathrm{n}_{2 ; " ;}(\mathrm{p})=1$, and $n_{2 ; \# ; a}(p)=1 \quad(\mathrm{Q} \quad \mathrm{p})$, where Q , the size of the pocket, is a variational param eter (in what follows we assum e Q $\quad t_{\text {? }}$ and hence the occupations of bands 3 and 4 are not a ected). P ictures of the non-interacting ground state and the trial state are shown in F ig. 33 and 3b. $N$ otice that the size of the pocket is the sam e in di erent channels because of the conservation of the num ber of electrons at half- lling. T his state breaks the SU (2), but not the $Z_{2}$ sym $m$ etry, and is therefore spin polarized (ferrom agnetic). There is a sim ilar state that breaks both sym $m$ etries and has no net $m$ agnetization: an electron (hole) pocket in the up (down) spin channel in $K$-point 1 and a hole (electron) pocket in the up (down) channel in $K$-point 2 . W e can show that the spin polarized state is low er in energy (see below).


FIG. 3: (C olor online) Sketch of the trial states: (a) H alf- lled non-interacting ground state, (b) Trial state w ith particle-hole pockets buitt upon (a), (c) D oped noninteracting ground state, (d) Trial state w ith particle-hole pockets built upon (c).

The change in the kinetic energy per unit area due to an electron (or hole) pocket of size Q is given by:

$$
\begin{equation*}
\frac{E_{k i n}}{S}=\frac{1}{2} \frac{\left(Q^{2}+t_{?}^{2}=4\right)^{3=2}}{3} \quad \frac{t_{?}^{3}}{24} \quad \frac{t_{?} Q^{2}}{4} \quad \frac{Q^{4}}{8 t_{?}} ; \tag{6}
\end{equation*}
$$

up to order $Q^{4}$. The expressions for the change in the exchange energy are cum bersom e and details are provided in A ppendix (C. We nd from Eq. (5), up to the sam e order:

$$
\begin{align*}
& \frac{E_{\text {ex }}(Q)}{S} \quad \frac{g}{8^{2}} \\
& \frac{8}{27} Q^{3} \quad \frac{h}{8}  \tag{7}\\
& +\frac{Z^{1}}{2} \ln \left(4=t_{?}\right)
\end{align*} \overline{4}_{0}^{\text {dyp } \frac{e^{d y}}{t_{?}^{2}=4+y^{2}}}{ }^{i^{Q^{4}}} \frac{t_{?}}{t_{?}}:
$$

$N$ otice that the leading order term in the exchange interaction is $E_{e x}=S \quad g Q^{3}=27^{2} \quad \mathrm{~m}^{3=2}$, where $m$ is the $m$ agnetization, which is alw ays dom inant over
the kinetic term that is of order $Q^{4} \quad \mathrm{~m}^{2}$. Therefore, we have proved that the bilayer is alw ays unstable to the form ation of polarized electron and hole pockets. In contrast to the single graphene plane case ${ }^{10}$, the total energy is negative for $s m$ all $Q$. $T$ his is due to the fact that the exchange with the lled bands is less im portant in this case. In order to calculate the equilibrium size of the pockets we $m$ inim ize the total energy, $E_{\text {tot }}(Q)=E_{k \text { in }}(Q)+E_{\text {ex }}(Q), w$ ith respect to $Q$ and nd $Q_{m}$ in , that is, the size of the pocket forw hich the energy is $m$ inim ized. For the param eters in graphene (see below ) we nd that $Q_{m}$ in $0: 05 t_{\text {t }}\left(t_{?}\right)$, justifying the above expansion.

C onsider the case where the system is initially doped w ith pockets of size $Q_{0}\left(n=Q_{0}^{2}=2\right)$. W e look for an instability by varying the density of electrons and holes sub ject to the constraint of particle conservation. N ote that the instability can produce one type of carrier (either electron or hole) if $Q_{0}>Q_{m}$ in or two type of carriers (electrons and holes) if $Q_{0}<Q_{m}$ in.$W$ e can param eterize the state $w$ th one type of carrier by taking $Q{ }_{n}^{2}=Q_{0}^{2}(2$
$\mathrm{x})$ and $Q_{\#}^{2}=Q_{0}^{2} \mathrm{x} w$ th $0 \quad \mathrm{x}$ 1. For the state w th two types of carriers we take instead $Q_{n}^{2}=2 Q_{0}^{2}+\dot{x} j$ and $Q_{\#}^{2}=j x j$ ith $x \quad 0$. The doped non-interacting ground state and the trialstate $w$ th particle-hole pockets ( $x<0$ ) are shown pictorially in Fig. 3c and 3d. T he calculation proceeds as before and we nd:

$$
\begin{align*}
\frac{E}{S} \quad \frac{1}{2 S} \quad E_{\text {tot }}\left(Q_{n}\right)+\quad E_{\text {tot }}\left(Q_{\#)}\right) & 2 E_{\text {tot }}\left(Q_{0}\right) \\
+ & E_{\text {extra }}\left(Q_{0} ; x\right): \tag{8}
\end{align*}
$$

The extra term, $E_{\text {extra }}\left(Q_{0} ; x\right)$, com es from term $s$ that cancel out in the undoped case. To leading order in $Q$ these term $s$ are given by $g Q_{0}^{4}(1 \quad x)^{2}=(64)$ for $x \quad 0$ and $g Q_{0}^{2}\left(Q_{0}^{2}+2 \dot{j} \bar{j}=(64)\right.$ when $x \quad 0$. In our units we havet? 1 so that, to a rst approxim ation, this contribution is much sm aller than the quartic term in Eq. (7), and it can be neglected. This leaves usw ith the rst line in Eq. (8) involying $E$ tot only. The dependence on $x$ is im plicit through $Q_{"}$ and $Q_{\#}$. Then Eq. (8) has the form : $E(Q)=A \not Q\}^{3}+B$ 过 ${ }^{4}$. Rescaling the $Q$ variable so that the $m$ in im a of the energy in the param agnetic states sits at $\mathbb{D} j=1$, we have:

$$
\begin{equation*}
E(Q)=X^{3}=3+\mathbb{S} \int^{4}=4: \tag{9}
\end{equation*}
$$

U sing the scaled variables we see that the system is unstable to $s m$ all deviations in $x$ from 1 if $Q_{0} \quad 1=2$. The ferrom agnetic state has low er energy than the param agnetic states if $Q_{0}<0: 7$ and the resulting state has electron and hole pockets. A s a consequence of the rst order nature of the transition, the system exhibits phase coexistence (that can be obtained from a M axw ell construction, not shown in the Fig. 4D, and hysteresis in physical properties such as m agneto-transport, around the critical line. In this region, the system show s a tendency tow ards electronic phase separation ${ }^{13}$, frustrated by electrostatic e ects. A s the charge densities involved
are rather low (see below) we cannot exclude the form ation of large dom ains of the di erent phases. The phase diagram fort? $=0: 05$ is show $n$ in $F$ ig. 4 as wellas a plot of $E\left(Q_{0} ; x\right)$ for som e typical cases of $Q_{0}$.


FIG. 4: (C olor online) Left: Phase diagram of the graphene bilayer as a function of electron density away from halflling, n (electrons per carbon), and coupling strength, $\mathrm{g}=$ $e^{2}=\left(0 V_{F}\right)$, with $t_{?}=0: 05$. Inset: $E$ as a function of $x$ (as de ned in the text) in the param agnetic (A), critical (B), and ferrom agnetic (C) regions of the phase diagram .

In the previous calculation we have not included the exchange interaction betw een di erent $K$-points in the $B$ rillouin zone. In that case the spin polarized state that breaks $S U(2)$ is degenerate $w$ ith the state that breaks both $S U(2)$ and $Z_{2}$. The di erence between the states is how the pockets are assigned to the spins and the $K$-points. By including exchange betw een $K-$ points in Eq. (5) we nd that there is sm all energy di erence between the states favoring a state with a net ferrom agnetism but which retains the $Z_{2}$ symmetry. Q uite generally this is the case since the elem ents of ${ }_{i j}\left(p^{0} ; p\right)$ ji $\left(p ; p^{0}\right)$ are all positive. A direct calculation using Eq. (5) and taking $p$ and $p^{0}$ to lie at nearest neighboring $K$-points con m sthis picture. O ne then nds a very sm all energy di erence of order / $Q^{4}$, and hence othere ects can be im portant in determ ining the actual ground state. There is also a correction to the $Q^{4}=t$ ? term in Eq. (7) that changes the position of the optim al value of $Q_{m}$ in by a sm allam ount.

In order to com pare $w$ ith experim ents it is interesting to estim ate the total $m$ agnetization in the polarized state for the case of the undoped graphene bilayer. W e estim ate the cut-o using a D ebye approxim ation so the the num ber of states is conserved in the B rillouin zone:
${ }^{2}=2=A_{u}=4=\left(\overline{27} a^{2}\right)$, where $A_{u}$ is the area of the real space unit cell. Restoring the units, we set $\mathrm{v}_{\mathrm{F}}=$ $30 \mathrm{a}=2 \quad 10^{6} \mathrm{~m} / \mathrm{s}$, and $\mathrm{t}_{?}={ }_{1}=\left(\mathrm{v}_{\mathrm{F}}\right.$ ) $5: 2 \quad 10^{2}$, where $1 \quad 0: 37 \mathrm{eV}$ is the typicalgraphite valué. H ence, for tw o pockets of size $Q$ the density of electrons per carbon is approxim ately $n=Q^{2}=4 \quad 1: 6 \quad 10^{6}$ ( $t_{\text {? }} \quad 0: 05$ and $Q \quad 0: 05 t$ ), and therefore, the $m$ agnetization per carbon ism $10^{6} \quad 10^{5} \mathrm{~B}$ ( B is the B ohrm agneton). $T$ hese num ber are, of course, very approxim ate because the value of them icroscopic param eters do not need to be
the sam e as in graphite and the presence of cut-o introduces fiurther uncertainty. In any event, the $m$ agnetized state of the graphene bilayer show s very weak ferrom agnetism. A direct experim ental consequence of our calculation is that the bilayerhas tw o species ofelectrons (electrons and holes) and therefore they should contribute to the $H$ all resistivity at $s m$ all $m$ agnetic elds, B. In particular, it is easy to show that the $m$ agneto-resistance at sm allm agnetic elds acquires a $\mathrm{B}^{2}$ dependence ${ }^{14}$.

## IV. OTHER HOPPING PARAMETERS

W ewould like to com ment on othere ects that we have not considered in the previous calculation. In term s of the Slonczew ski-W eiss M © lure m odel for graphite ${ }^{15,16}$ our model includes only the param eters 0 ( t ) and 1 ( $t_{\text {? }}$ ) but not 3 and 4 . On the one hand, 4 introduces an electron-hole asym $m$ etry by changing the curvature of the bands, but the bands rem ain parabolic near half
lling. On the other hand, 3 introduces a trigonal distortion which restores a linear dispersion at low energies. To estim ate the ects of 3 we use the e ective lowenergy $m$ odel that can be derived from the extension of Eq. (3) to include 3 and pro jecting onto the two bands that are closest to the Ferm i surface (see Ref. [17] and A ppendix 国 for details). Thee ective kinetic energy m atrix is then:

$$
\begin{equation*}
K(p)=\frac{p^{2}}{t_{?}} e_{e^{i 2}}^{0} e^{i 2} \quad+v_{3} p e^{i} e^{0} \quad ; \tag{10}
\end{equation*}
$$

w here $\mathrm{v}_{3}={ }_{3}=0, \mathrm{w}$ ith energy eigenvalues given by:

$$
E \quad(p)=\quad \frac{p}{p} \overline{p^{2}+\left(v_{3} t_{?}\right)^{2}+2 p v_{3} t_{?} \cos \beta \quad(p)}=t_{?}:(11)
$$

It is easy to see that the crossover from linear to quadratic dispersion takes place at a mom entum pcross $v_{3} t_{\text {? }}$. If $p_{\text {cross }} \quad Q_{m}$ in ( $v_{3} \quad 0: 1$ ) the previous calculation is still valid since the dispersion rem ains parabolic at the scale of the instability. $N$ evertheless, if one uses the values of the param eters in the graphite literature ${ }^{6}$, nam ely, $v_{3}={ }_{3}=0 \quad 0: 1 \mathrm{we}$ conclude that pross $\quad Q_{m}$ in and the trigonal distortion $m$ ay becom e im portant. W e should rem ark, once again, that it is not guaranteed that the value of the param eters in graphite are the sam e as in the bilayer (hence, one should take the num bers here with a grain of salt). At sm all energies, the spectrum in Eq. (10) can be described in term s of one D irac cone at $p=0$, and three asym $m$ etric cones at $p_{\text {cone }}=v_{3} t_{\text {? }}$. (the direction of the cones are such that $\cos (3)=1$ ). $T$ his situation $m$ aps onto the single graphene plane case ${ }^{10}$ w ith ellipsoidal pockets instead of circular, and a sm all renom alized Ferm i velocity, $\mathrm{V}_{\mathrm{F}} \quad \mathrm{V}_{3} \mathrm{~V}_{\mathrm{F}}\left(\mathrm{v}_{\mathrm{F}}\right)$. Therefore the dim ensionless coupling strength is $g=g=v_{3}$ 20, which is much larger than the critical coupling for ferrom agnetism ${ }^{10}$. Then, in this case the transition from param agnetism is into a fully polarized state with e ective bandw idth oforder of $v_{3} t_{\text {? }}$, leading to a polarization

Of the order of $10{ }^{6}$ electrons per carbon, which is of the sam e order of $m$ agnitude of polarization found $w$ thout 3. U nfortunately this argum ent is not rigorous since the exchange w th the lled bands also contributes, requiring a m ore detailed study.

## V. SHORTRANGEINTERACTIONS

W e consider thee ects ofshort-range electron-electron interactions which, for sim plicity, we describe by an onsite H ubbard interaction, U. It tums out that this interaction favors an antiferrom agnetic ordering. In order to quantify the tendency tow ards this phase, we calculate the associated susceptibility and present a sim ple m ean eld argum ent.
A. E lectron ic susceptibility.

U sing the basis de ned in Eq. (10) w ith $v_{3}=0$ (the procedure outlined in Appendix El the wavefiunctions corresponding to the tw o bands closest to the Ferm ilevel can be w ritten approxim ately as:

$$
\begin{equation*}
\text { (k) } p_{\overline{2}}^{1} e^{i(k)} e^{\dot{j}(k)} \text {; } \tag{12}
\end{equation*}
$$

so that the states are m ostly localized at the sites w ithout a corresponding atom in the neighboring layer. Form ally, this tw o com ponent wavefunction is equivalent to
the spinor de ned in the analysis of a single graphene plane except that the angle is doubled. R estricting the calculation to this subspace, we can w rite the bare susœeptibility as a 2 m atrix ( Ref 18) :

$$
0(q ;!)=\quad \begin{array}{cc}
\mathrm{D}(q ;!) & \text { ND }(q ;!) \tag{13}
\end{array} \quad:
$$

Here $D$ denotes the response in the sam e plane as the source and ND response in the opposite plane. The random phase approxim ation (RPA) susceptibility, assum ing an on-site $H$ ubbard interaction $U$, is:

$$
\begin{equation*}
\operatorname{RPA}(q ;!)=0(q ;!) 1 \quad U \quad 0(q ;!)^{1}: \tag{14}
\end{equation*}
$$

$T$ his expression becom es sim pler when decom posed into a contribution sym $m$ etric in the two sublattioes and another antisym m etric:

$$
\begin{align*}
& \frac{\mathrm{FM}(q ;!)}{4}=\frac{\mathrm{D}(q ;!)+\mathrm{ND}(q ;!)}{1 \mathrm{U}[\mathrm{D}(q ;!)+\mathrm{ND}(q ;!)]} ; \\
& \frac{\mathrm{AFM}(q ;!)}{4}=\frac{\mathrm{D}(q ;!) \mathrm{ND}(q ;!)}{1 \mathrm{U}[\mathrm{D}(q ;!) \mathrm{ND}(q ;!)]}: \tag{15}
\end{align*}
$$

The sym $m$ etric susceptibility gives the response of the system to a magnetic eld which is the same in the two sublattioes (note that we are neglecting the in uence of the sites where the states have zero weight of $k=0$ ), and induces a ferrom agnetic ordering. The antisym $m$ etric response leads to antiferrom agnetic ordering. T he susceptibilities can be w ritten as:
where $k+q=2 ; k \quad q=2$ is the angle betw een $k+q=2$ and $k \quad q=2$, and:

$$
\begin{equation*}
\cos ^{2} \quad k+q=2 ; k \quad q=2=\frac{(k+q=2) \quad(k \quad q=2)^{2}}{k+q=2 j k \quad q=2 j}=\frac{\left(k^{2} \quad q^{2}=4\right)^{2}}{\left(k^{2}+q^{2}=4\right)^{2} \quad k^{2} q^{2} \cos ^{2}()} \tag{17}
\end{equation*}
$$

The only dependence on the angle betw een the vectors $k$ and $q$ of the expressions in Eq. (16) is (after using the double angle form ula) through the cosine in Eq. (17). A veraging over angles, we obtain:

$$
\begin{equation*}
\cos ^{2} \quad k+q=2 ; k \quad q=2=\frac{\dot{k} \hat{j} \quad \dot{q} \hat{j}=4}{\dot{k} \hat{\jmath}+\dot{q} \dot{\jmath}=4}: \tag{18}
\end{equation*}
$$

Inserting this expression into Eq . (16) it is a sim ple task to perform the rem aining one-dim ensional integral. Introducing $\underset{F M}{0}=D(q ;!)+{ }_{N D}(q ;!)$ and $\underset{A F M}{0}={ }_{D}(q ;!) \quad N D(q ;!)$ we can extract the leading dependence on the
cut-o of the susceptibilities, and we nally obtain:

$$
\begin{align*}
& \operatorname{Im} \underset{A F M}{0}(q ;!)=\frac{t_{?}}{8} \quad j!j \frac{\dot{q}{ }^{f}}{2 t_{?}} \operatorname{sign}(!) \quad \operatorname{Im} \underset{F M}{0}(q ;!): \tag{19}
\end{align*}
$$

H ence, setting $q=0$, the antiferrom agnetic susceptibility diverges logarithm ically with the cut-o for any nite frequency !. The logarithm ic dependence im plies the existence of an instability for any positive value of the interaction U.A ltematively, we can show the existence of th is instability by a direct calculation of the correlation energy gained by polarizing the system.

It is worth noting that the divergence obtained here, and the related $m$ arginal.behavior of a local interaction can be obtained from the sam e pow er counting argum ents used for the analysis of tw o dim ensional interacting electrons near a van $H$ ove singularity ${ }^{19}$. If we include next nearest neighbor couplings through the param eter 3, as discussed in Section IV, the low energy bands can be described by an e ective $D$ irac equation. The screening of the long range $C$ oulom $b$ interaction vanishes, and the corresponding susceptibility can also be calculated analytically $y^{20,21}$.
$N$ ote also that the polarization function is sim ply related to the susceptibilities ${ }^{22}$ above by ${ }^{0}={ }^{0}$. This allows one to get the screening properties within the RPA easily. In particular, for the mode that is sym $m$ etric in the layer densities which originally had the long-w avelength $1=\dot{q} j$ singularity the static $(!=0)$ RPA screening cuts o the singularity by taking $1=\dot{j} j$ ! $1=\left(j_{j} j+q_{F}\right)$. From Eq. (19) we nd that the Thom as Ferm i screening wavevector $q_{F}$ / $t_{?}$. This is in agreem ent w th what one expects from the usual twodim ensionalelectron gas w here the screening w ave-vector is $/ \mathrm{m}$ independently of the density of carriens $\mathrm{s}^{23,24}$.

> B. M ean- eld approach

A ltematively we can explain the diverging susceptibilIty $w$ ith a simple $m$ ean- eld approach. $W$ e introduce a staggered $m$ ean- eld into the $H$ am iltonian according to
where the label di erent spin orientations. The four bands are then:

$$
\begin{equation*}
(k)=\frac{s \overline{2 k^{2}+t_{?}^{2}+2^{2} t^{p} \overline{4 k^{2}+t_{?}^{2}}}}{2}: \tag{21}
\end{equation*}
$$

$T$ he opening of the gap lowers the kinetic energy of the system. W e estim ate this by perform ing the integral up to $\mathrm{k}=\quad=1$, then forto $=: 05$

$$
\begin{equation*}
E_{k i n} \quad 21: 9043 \quad \frac{t_{?}}{2} \ln ()^{2}+O\left({ }^{3}\right) ; \tag{22}
\end{equation*}
$$

is the change in the kinetic energy per unit cell due to . The connection betw een the average $m$ agnetization $\left.M=j<n_{j ; "}\right\rangle \quad<n_{j ; \#}>j$ and the $m$ ean eld is $=$ $U M=2$, where $U$ is the strength of the on-site $H$ ubbard interaction. T he energy price one $m$ ust pay per unit cell for having doubly occupied sites is

$$
\begin{equation*}
E_{U}=U M^{2}=\frac{4}{U}^{2}: \tag{23}
\end{equation*}
$$

Because of the logarithm in Eq. (22) a sm all antiferrom agnetic distortion is alw ays favorable. A ssum ing that is sm all, the $m$ ean- eld solution is:

$$
\begin{equation*}
\text { MF } \quad \exp \frac{1}{2} \frac{2=U \frac{1: 9043}{t_{?}=2} ;}{} \tag{24}
\end{equation*}
$$

and hence is exponentially suppressed unless $U$ is of the order of . O ther variations of the m ean- eld in Eq. 20) give sim ilar results. Thusw ithin the m ean- eld approxi$m$ ation, the anti-ferrom agnetism found here is very w eak unless the interaction is strong.

## VI. CONCLUSIONS

In sum $m$ ary, we have show $n$ that long-range $C$ oulom b interactions in a clean graphene bilayer lead to a ground state that is magnetically polarized with electron and hole pockets. W e have determ ined the phase diagram of thism odelas a function ofthe coupling strength and doping, w ith a rst order phase transition line betw een the
param agnetic and ferrom agnetic states. A round the critical line one expects hysteresise ects associated $w$ th the presence of phase coexistence and/orm agnetic dom ains. W e have also show $n$ that on-site electron-electron interactions produce a staggering of the ferrom agnetic order in the two planes and hence, c-axis antiferrom agnetism . $T$ he introduction of other term $s$ in the $H$ am iltonian, such as trigonal distortions, $m$ akes the phase diagram even richer, due to the creation of new energy scales. It is clear from our studies that graphene bilayers present an electronic behavior that is rather di erent from ordinary $m$ etals. T he study of these system $s$ becom es even $m$ ore relevant given the recent developm ents in the fabrication and control of graphene multi-layers, and their possible application in nano-electronics.

A cknow ledgm ents
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## APPENDIXA:UNITARYTRANSFORMATION

The unitary transform ation $M \mathrm{p}$ that one needs to diagonalize the H am iltonian in Eq. (3) can be written as $M_{p}=M_{1}(p) M_{2} M_{3}(p)$, where

$$
M_{1}(p)=\begin{array}{cccccc}
0 & 1 & 0 & 0 & 0 & 1 \\
B & 0 & e^{i}(p) & 0 & 0 & C  \tag{A1}\\
B & 0 & 0 & 1 & 0 & A \\
0 & 0 & 0 & e^{i}(p)
\end{array}
$$

is a gauge transform ation,

$$
\begin{align*}
& { }^{0} 100100^{1} \\
& M_{2}=P_{\overline{1}}^{1} \stackrel{B}{Q} \begin{array}{lllll}
0 & 1 & 0 & 1 & C \\
1 & 0 & 1 & 0 \\
0 & 1 & 0 & 1
\end{array} \tag{A2}
\end{align*}
$$

form $s$ sym $m$ etric/antisym $m$ etric bands, and

| M 3 (p) $=$ B | $\left.\operatorname{cos[}{ }^{(p)}\right] \sin \left[{ }^{\prime}(p)\right]$ | 0 | 0 |
| :---: | :---: | :---: | :---: |
|  | $\sin \left[{ }^{\prime}(p)\right] \cos \left[{ }^{\prime}(p)\right]$ | 0 | 0 |
|  | 00 | $\cos \left[{ }^{\prime \prime}(p)\right]$ | $\sin \left[{ }^{[ }(\mathrm{p})\right]^{\text {A }}$ |
|  | 00 | $\sin \left[{ }^{1}(p)\right]$ | $\left.\cos ^{[1}(\mathrm{p})\right]$ |

takes care of the nal diagonalizing rotation. C hoosing $\tan \left[2^{\prime}(p)\right]=2 p=t_{\text {? }}$ the rotated $H$ am iltonian $K_{\text {diag }}(p)=$ $M \underset{\mathrm{p}}{\mathrm{y}} \mathrm{K}(\mathrm{p}) \mathrm{M} \mathrm{p}^{2}$ becom es diagonal:

$$
\begin{array}{ll}
K_{\text {diag }}(p)=\text { diag } & t \quad=2 \quad E(p) ; \quad t=2+E(p) ; \\
& t_{?}=2+E(p) ; t_{?}=2 \quad E(p): \tag{A4}
\end{array}
$$

Except for the labeling of the states (1 4), which is just a perm utation, this is the unitary transform ation we need to diagonalize the non-interacting problem.

## APPEND IX B: EXCHANGE INTEGRALFOR BLOCH ELECTRONS

Quite generally the H artree Fock energy consists of three term s. A kinetic term, a direct charging term, and an exchange term. The exchange term is $\mathrm{i}^{25}$

$$
\begin{equation*}
\mathrm{E}_{\mathrm{ex}}={ }_{\mathrm{m} ; \mathrm{n}}^{\mathrm{X}}<\mathrm{m} ; \mathrm{n} \ddagger \mathrm{j} \text { n; } ; \mathrm{m}>; \tag{B1}
\end{equation*}
$$

$w$ here $V$ is the interaction potential and the sum is over occupied states. Expanding in B loch states $k$; we get

$$
\begin{equation*}
\mathrm{E}_{\mathrm{ex}}=\mathrm{X}_{\substack{\mathrm{k} ; ; \mathrm{n}_{\mathrm{k}} ; \\ \mathrm{k}^{\circ} ;{ }^{0}}}^{\mathrm{n}} \mathrm{n}_{\mathrm{k} 0} ; 0 ; \mathrm{J}_{\mathrm{k} ; \mathrm{k}^{0}} ; \tag{B2}
\end{equation*}
$$

where for the unscreened C oulom b interaction in 2D

$$
\begin{align*}
J_{k ; k^{0}}^{;}{ }^{0}=\frac{e^{2}}{2} & { }^{Z} d^{2} x^{Z} d^{2} x^{0} \\
& \frac{k ;(x) k^{0} ; \circ(x) k^{0} ; \circ\left(x^{0}\right) k ;\left(x^{0}\right)}{x^{0} j}: \tag{B3}
\end{align*}
$$

Let us consider one plane only, then we can write the $B$ loch states in the tight-binding approxim ation as

$$
\begin{align*}
& +\quad e^{i k}{ }^{T_{B}} b_{k} ; W\left(\begin{array}{ll}
x & T_{B}
\end{array}\right) \text {; } \tag{B4}
\end{align*}
$$

where $w(x)$ is the localized basis function, $T_{A}\left(T_{B}\right)$ are the lattioe vectors of lattice $A(B)$ and $a_{k}$; and $b_{k}$; are the functions that generate the $B$ loch state in question. N eglecting the overlap of w ave-finctions on the A and B sites we get approxim ately

$$
\begin{aligned}
& \left.k ;(x) \quad k^{0} ; 0(x) \quad e^{j\left(k^{0}\right.} k\right) \quad x^{x}=S
\end{aligned}
$$

The functions $A$ and $B$ are periodic in the real-space lattice and can hence be expanded in com ponents of harm onics of the reciprocal lattice fK g . K eeping only the leading constant term com ing from the $K=0$ term $s$ we get $=1$, in which case

$$
\begin{align*}
\mathrm{J}_{\mathrm{k} ; \mathrm{k}^{0}}{ }^{0}=\mathrm{a}_{\mathrm{k}} ; & \mathrm{a}_{\mathrm{k} 0} ;{ }^{0}+\mathrm{b}_{\mathrm{k}} ; \mathrm{b}_{\mathrm{k} 0} ; 0 \\
& \mathrm{a}_{\mathrm{k} 0} ;{ }^{\circ} \mathrm{a}_{\mathrm{k}} ; \tag{B6}
\end{align*}
$$

$T$ he corrections to this $K=0$ term are dow $n$ by at least a factor of $\mathrm{k} \quad \mathrm{k}^{0} \mathrm{\jmath}$ as is explained in Ref . 25]. It is possible to include higher harm onics in the reciprocal lattioe, but then the im portant divergence near $k \quad k^{0}$ is cut-o by $K$. M oreover, including $K \in 0$ we should also include
short-range (high energy) physics that is not described by the continuum modelused here.
$N$ ote also that the expression in Eq. (B6) is just what one get from a sim ple Fourier transform if one also includes the spinor structure due to the two sub-lattioes. W e apply this to the bilayer where the C oulom b interaction can be written

$$
\begin{aligned}
H_{I} & =\frac{1}{2}^{Z} d^{2} x d^{2} y^{n} V^{D}(x \quad y) l_{1}(x)_{1}(y)+{ }_{2}(x)_{2}(y) \\
& \left.+V^{N D}(x \quad y)_{1}(x)_{2}(y)+{ }_{1}(x)_{2}(y) \quad: \quad \text { (B } 7\right)
\end{aligned}
$$

W e Fourier transform this and introduce the sym $m$ etric and antisym $m$ etric com binations

$$
\begin{equation*}
(q)=1(q) \quad 2(q): \tag{B8}
\end{equation*}
$$

to $w$ rite the interaction in a diagonal form

$$
\begin{equation*}
H_{I}=\frac{1}{2 S}_{q}^{X^{0} X} \quad(q) V \quad(q) \quad(q) ; \tag{B9}
\end{equation*}
$$

where $V=\frac{2 e^{2}}{0 q}\left(1 \quad e^{q d}\right)=2$. The prim e on the $q$-sum denotes that the $q=0$ term should be excluded since it is canceled by the positive (jellium ) background. In term s of the operators that diagonalizes the kinetic term $s$ the density operators can be w ritten as

$$
\begin{equation*}
(q)={\underset{p}{X} \underset{p+q}{y}(p+q ; p) p ; ~}_{p} \quad(p) \tag{B10}
\end{equation*}
$$

where

$$
\begin{align*}
& { }^{0} 100000^{1} \\
& (p+q ; p) \quad M \underset{p+q}{Y} \underset{C}{B} \begin{array}{llllll}
0 & 1 & 0 & 0 & C \\
0 & 0 & 1 & 0 \\
0 & 0 & 0 & 1
\end{array} \tag{B11}
\end{align*}
$$

and $M_{p}$ is given in A ppendix A. U sing this one can easily generalize Eq. (B2) and (B6) to arrive at Eq. (5).

## APPENDIXC:EXCHANGE INTEGRAL

$U \operatorname{sing} V^{D}(q)=2 g=q$ and $V^{N D}(q)=2$ ge $q d=q$ one quite generally get that the change in the exchange energy can be w ritten as

$$
\begin{align*}
& <\frac{\mathrm{H}_{\mathrm{I}}}{\mathrm{Z}^{\mathrm{I}}}>= \\
& \frac{1}{2} \frac{d p}{(2)^{2}} \frac{d^{0}}{(2)^{2}}{ }^{2} 2 \quad\left(Q \quad \text { p) } K_{1}^{D} V^{D}+K_{1}^{N D} V^{N D}\right. \\
& +\quad(\mathrm{Q} \quad \mathrm{p})(\mathrm{Q} \quad \mathrm{~B}) \mathrm{K}_{2}^{\mathrm{D}} \mathrm{~V}^{\mathrm{D}}+\mathrm{K}_{2}^{N D} V^{N D}{ }^{\circ} \tag{C1}
\end{align*}
$$

$T$ he $K$ 's are sum $s$ of certain com ponents of the $m$ atrioes ${ }_{i j}\left(p^{0} ; p\right)=i j^{i j}\left(p^{0} ; p\right){ }_{j i}\left(p ; p^{0}\right) . N$ ote that the elem ents of are all greater or equal to zero.

$$
\text { 1. } \mathrm{H} \text { alf- lling }
$$

At half-lling the trial state is characterized by the single variational param eter $Q$. It is straightforw ard, albeit tedious, to perform the $m$ atrix $m$ ultiplications and extract the $K$ 's. The results for an electron and a hole pocket of size $Q$ is:

$$
\begin{equation*}
K_{1}^{D}=\frac{p}{E(p)} \frac{p^{0}}{E\left(p^{0}\right)} \cos \left({ }^{0}\right) ; \tag{C2}
\end{equation*}
$$

$$
\begin{align*}
& K_{1}^{N D}={\frac{t}{2 E\left(p^{0}\right)}}^{n} 1 \frac{t}{E(p)} \quad 1+\frac{t}{E(p)} \cos 2\left(\quad{ }^{0}\right) ;  \tag{C3}\\
& K_{2}^{D}=\frac{1}{2} \frac{p}{E(p)} \frac{p^{0}}{E\left(p^{0}\right)} \cos \left({ }^{0}\right)+\frac{1}{2} 1+\frac{t}{E(p)} \frac{t}{E\left(p^{0}\right)} ; \tag{C4}
\end{align*}
$$

$$
\begin{aligned}
K_{2}^{N D}= & \frac{1}{2} \frac{p}{E(p)} \frac{p^{0}}{E\left(p^{0}\right)} \cos \left({ }^{0}\right) \\
& +\frac{1}{4} 1 \frac{t}{E(p)} 1 \frac{t}{E\left(p^{0}\right)} \\
& +1+\frac{t}{E(p)} 1+\frac{t}{E\left(p^{0}\right)} \cos 2\left(\quad 0^{0}\right)^{0}:(C 5)
\end{aligned}
$$

In this appendix we tem porarily relabel $t_{?}=2!\quad t$ to avoid an excessive am ount of 2 's in the equations. W e can w rite

$$
\begin{equation*}
\left\langle\frac{\mathrm{H}_{\mathrm{I}}}{\mathrm{~S}}\right\rangle=\frac{\mathrm{gV}_{\mathrm{F}}{ }^{3}}{4^{2}} \mathrm{C}_{1}^{\mathrm{D}}+\mathrm{C}_{1}^{\mathrm{ND}}+\mathrm{C}_{2}^{\mathrm{D}}+\mathrm{C}_{2}^{\mathrm{ND}} ; \tag{C6}
\end{equation*}
$$

where we are $m$ easuring all param eters (ie. $Q$ and $t$ ) in units of the cut-o. The C's are given by the integrals

$$
\begin{align*}
& C_{2}^{D}=\frac{Q^{3}}{2} 0_{0}^{Z_{1}} x d x \sum_{0}^{Z} y d y d^{Z} Q^{2} p \frac{x}{t^{2}+(Q x)^{2}} p \frac{y}{t^{2}+(Q y)^{2}} \cos () \\
& +1+p \frac{t}{t^{2}+(Q y)^{2}} p \frac{t}{t^{2}+(Q x)^{2}} \quad \frac{1}{\dot{y} x j} \text {; } \\
& C_{2}^{N D}=\frac{Q^{3}}{4} 0_{0}^{Z} x d x \sum_{0}^{Z} y d y \sum_{0}^{Z} d \frac{e^{d Q i y} x j}{\dot{y} x j} 2 Q^{2} p \frac{x}{t^{2}+(Q x)^{2}} P \frac{y}{t^{2}+(Q y)^{2}} \cos () \\
& +1 p \frac{t}{t^{2}+(Q x)^{2}} 1 \frac{t}{t^{2}+(Q y)^{2}}+1+p \frac{t}{t^{2}+(Q x)^{2}} 1+p \frac{t}{t^{2}+(Q y)^{2}} \cos (2): \tag{C7}
\end{align*}
$$

From this one can extract the leading and sub-leading term $s$ in an expansion in powers of $Q$, the result is given in Eq. (7). Som e useful expressions for perform ing the expansion are provided in A ppendix D.

## 2. D oped case

T he calculation for the doped system proceeds exactly as in the previous case but we m ust allow for the electron and hole pockets to have di erent size. For each electron (or hole) pocket of size $Q_{e}\left(Q_{h}\right)$ there is a contribution like that in Eq. (C1). The K's are halfof those in Eq. (C 3), (C 4) and (C5). But $K_{1}^{D}$ is di erent for holes and electrons:

$$
\begin{equation*}
K_{1 e=h}^{D}=\frac{1}{2} \frac{p^{0}}{2 E(p) E\left(p^{0}\right)} \cos (): \tag{C8}
\end{equation*}
$$

The contributions com ing from the $1=2$ are easy to obtain and can be encoded in a new contribution $C_{\text {new }}$ in Eq. (C 6), where

$$
\begin{equation*}
C_{\text {new }}=Q^{2} R_{0}(Q) ; \tag{C9}
\end{equation*}
$$

and $R_{0}$ is given in A ppendix D.

## APPEND IX D:COULOM B INTEGRALS

Let us de ne


Then one can show that up to $O\left(Q^{10}\right)$

$$
\begin{aligned}
R_{0}(Q)= & \frac{h}{2} 1 \frac{Q^{2}}{8} \frac{Q^{4}}{64} \frac{5 Q^{6}}{1024} \frac{35 Q^{8} i}{16384} ; \\
R_{1}(Q)= & \frac{-}{6} Q \ln (Q)+\frac{\overline{3} \ln (2) \quad \frac{1}{12} Q}{} \\
& \frac{h_{3 Q^{3}}^{2}}{\frac{30}{80}+\frac{15 Q^{5}}{1792}+\frac{175 Q^{7}}{55296}+\frac{2205 Q^{9} i}{1441792} ;} \\
R_{2}(Q)= & \frac{2}{9} Q \quad-\frac{3 Q^{2}}{16}+\frac{5 Q^{4}}{288}+\frac{21 Q^{6}}{4096}+\frac{9 Q^{8}}{4096}:
\end{aligned}
$$

M oreover $R_{0}(1)=4=3, R_{0}(1)=2(2 C \quad 1)=3$ and $R_{2}(1)=$ $4(3 \quad 7)=27 . C \quad 0: 91596$ is the $C$ atalan constant.

## APPENDIX E:APPROXIMATE TWOBAND M ODELS

There are two reasons for constructing approxim ate tw o-band m odels. F irstly, on physical grounds the highenergy bands should not be very im portant for the low energy properties of the system . Secondly, it is much easier to work w th 22 m atriges instead of 4 m atrices. In this appendix we derive the low-energy e ective model by doing degenerate second order perturbation theory. $T$ he quality of the expansion is good as long as $v_{F} p \quad t_{\text {? }}$.

1. Sim ple low -energy m odel

If we transform the H am iltonian m atrix in Eq. (3) by taking the sym $m$ etric and anti-sym $m$ etric com binations of the rst and third rows (and colum ns) we can write $\mathrm{H}_{\mathrm{k} \text { in }}=\mathrm{H}_{0}+\mathrm{H}_{1}$, where

$$
\mathrm{H}_{0}=\begin{array}{ccccc}
0 & \mathrm{t} & 0 & 0 & 0^{1}  \tag{E1}\\
\mathrm{~B} & 0 & 0 & 0 & 0 \mathrm{C} \\
\mathrm{O} & 0 & 0 & \mathrm{t}_{?} & 0^{\mathrm{A}} ; \\
0 & 0 & 0 & 0
\end{array}
$$

Perform ing second order perturbation theory one nds an e ective $H$ am iltonian matrix, $H_{e}=H_{1}^{y}\left(1=H_{0}\right) H_{1}$, where:

T he low energy spinors are then given by:
and the corresponding energies are $p^{2}=t_{\text {? }}$. If we add the contribution from 3 (which is already diagonal in this basis) and only keep the B -atom com ponents we im $m$ ediately arrive at Eq. (10).

In fact it is easier to see the existence of the exchange instability in this basis. W orking in this subspace we again get an expression like that in Eq. (C1) w ith $K_{1}^{D}=0, K_{1}^{N D}=\cos (2), K_{2}^{D}=1$ and $K_{2}^{N D}=\cos (2)$. If one further neglects the di erence betw een $\mathrm{V}^{\mathrm{D}}$ and $V^{N D}$ the resulting change in the exchange energy can be expressed w th the help of the functions de ned in Appendix D. Explicitly the leading term in the exchange energy is / $\quad Q^{3} R_{0}(1)+R_{2}(1)+2 Q^{2} R_{2}(Q) \quad 8 Q^{3}=27$ in agreem ent with the result in Eq. (7).

## 2. $M$ ore general low -energy m odel

A $m$ ore general $H$ am iltonian $m$ odel for the low energy physics is given by ${ }^{\frac{3}{3}}$ :

O ne can perform a unitary transform ation so that $\mathrm{H}_{2}=$ $M{ }^{Y_{H}}{ }_{0} M$, where $M=M_{1}(p) M_{2}$ and $M_{1}(p)$ and $M_{2}$ are given in Eq. (A1) and (A 2). W e may then separate the transform ed H am iltonian into three parts, $\mathrm{H}_{2}=\mathrm{K}_{0}+$ $\mathrm{K}_{1}+\mathrm{K}_{2}$, w ith:
$W$ ith this decom position it is easy to nd the approxi$m$ ate eigenstates and eigenvalues for $v_{F} p \quad t_{\text {? }}$.

For the high-energy states one can use the sim ple non-degenerate perturbation theory. The eigenvalues are given by $E_{3}=t_{?}+\left(v_{F}+v_{4}\right)^{2} p^{2}=t_{?}$ and $E_{4}=\quad t_{0} \quad\left(v_{4}\right)^{2} p^{2}=t_{?}$. It is also straightforw ard to obtain the corresponding states. For the low -energy sector the second order perturbation result (from two $K_{2}$ and one $K_{0}$ ) can give a term which is of the sam e order as that of $\mathrm{K}_{1}$. Thus, wem ust use degenerate perturbation theory. T he usualm anipulations then given the H am iltonian m atrix in the low energy subspace as $\mathrm{K}_{\text {low }}=\mathrm{K}_{1} \quad \mathrm{~K}_{2} \mathrm{P}_{1}\left(1=\mathrm{K}_{0}\right) \mathrm{P}_{1} \mathrm{~K}_{2}$, where $\mathrm{P}_{1}$ is the pro jection out of the low -energy subspace, explicitly
and the corresponding eigenvalues are

$$
\begin{equation*}
\frac{2 v_{F} v_{4} p^{2}}{t_{?}} \quad\left(v_{3} p\right)^{2}+\frac{h\left(v_{F}^{2}+v_{4}^{2}\right) p^{2} i_{2}}{t_{?}} \quad 2\left(v_{3} p\right) \frac{h\left(v_{F}^{2}+v_{4}^{2}\right) p^{2}}{t_{?}} \cos (3): \tag{E10}
\end{equation*}
$$

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